



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



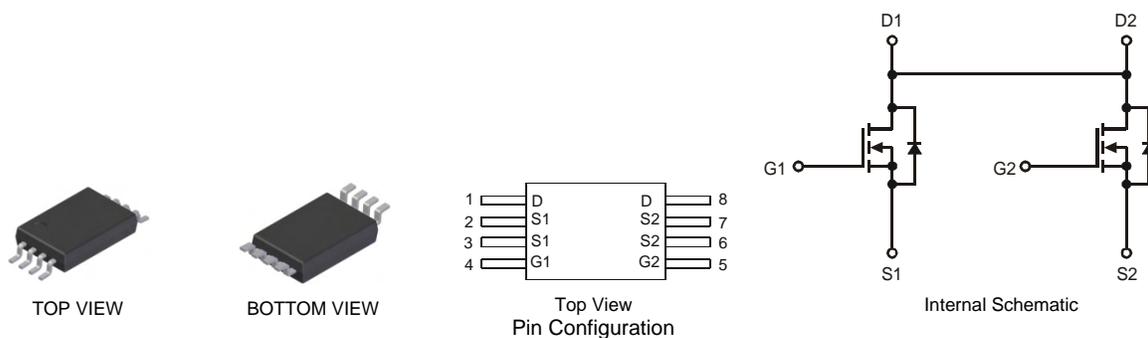
企业QQ二维码

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

Mechanical Data

- Case: TSSOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.039 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 3)	Steady State	$T_A = 25^\circ\text{C}$	I_D	6.7	A
		$T_A = 70^\circ\text{C}$		4.9	
Pulsed Drain Current (Note 4)			I_{DM}	30	A

Thermal Characteristics

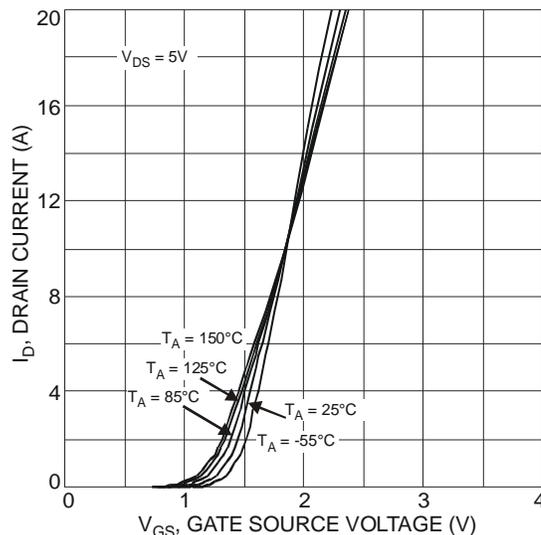
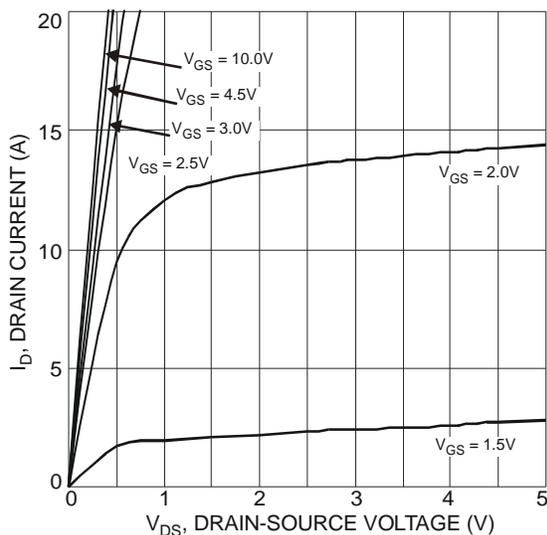
Characteristic			Symbol	Value	Unit
Power Dissipation (Note 3)			P_D	0.89	W
Thermal Resistance, Junction to Ambient @ $T_A = 25^\circ\text{C}$			$R_{\theta JA}$	140	$^\circ\text{C/W}$
Operating and Storage Temperature Range			T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 1. No purposefully added lead.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1.0	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	-	1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	19	26	m Ω	$V_{GS} = 4.5V, I_D = 6.0A$
			26	36		$V_{GS} = 2.5V, I_D = 5.2A$
Forward Transfer Admittance	$ Y_{fs} $	-	8	-	S	$V_{DS} = 10V, I_D = 6A$
Diodes Forward Voltage	V_{SD}	-	0.7	1.2	V	$I_S = 1.7A, V_{GS} = 0V$
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	570	-	pF	$V_{DS} = 10V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	85	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	75	-	pF	
Gate Resistance	R_g	-	1.23	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
SWITCHING CHARACTERISTICS (Note 6)						
Total Gate Charge	Q_g	-	5.2	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$ $I_D = 7A$
Gate-Source Charge	Q_{gs}	-	0.86	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.25	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	5.2	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$ $R_L = 1.5\Omega, R_G = 1\Omega$
Turn-On Rise Time	t_r	-	13.5	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	19.8	-	ns	
Turn-Off Fall Time	t_f	-	6.1	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effects.
6. Guaranteed by design. Not subject to production testing.



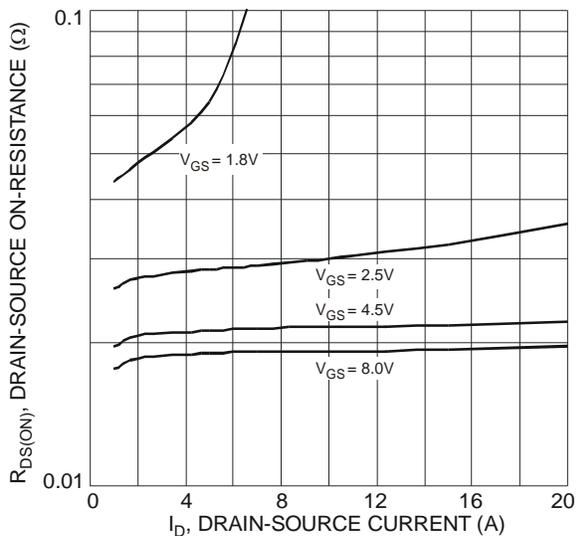


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

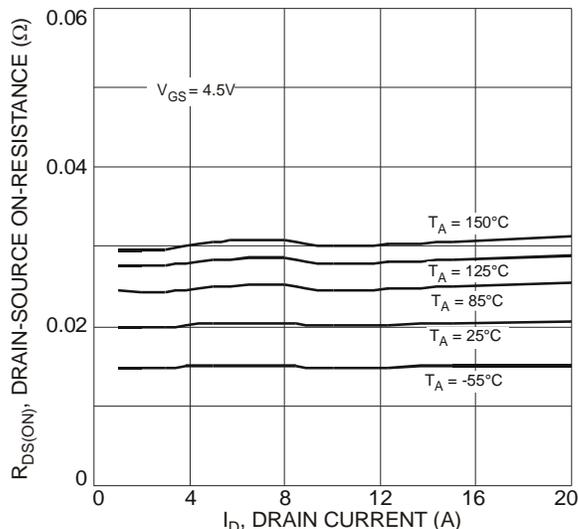


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

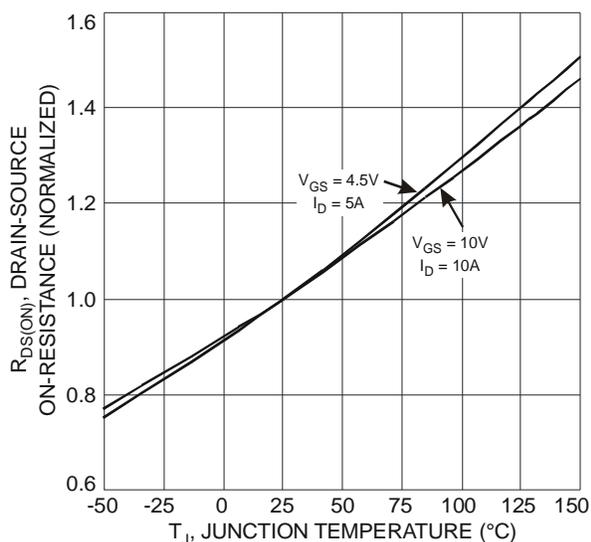


Fig. 5 On-Resistance Variation with Temperature

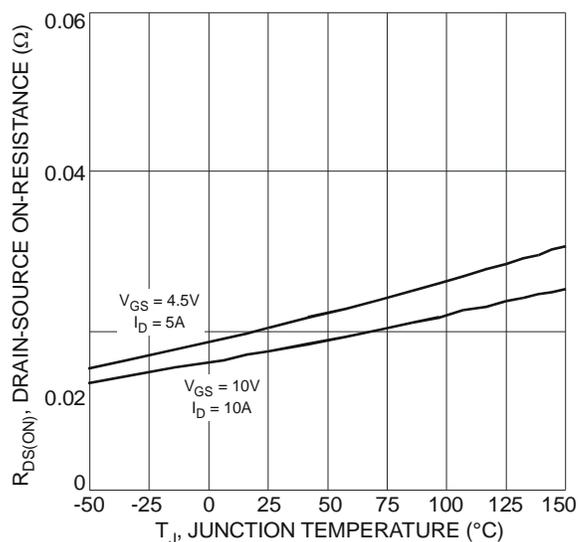


Fig. 6 On-Resistance Variation with Temperature

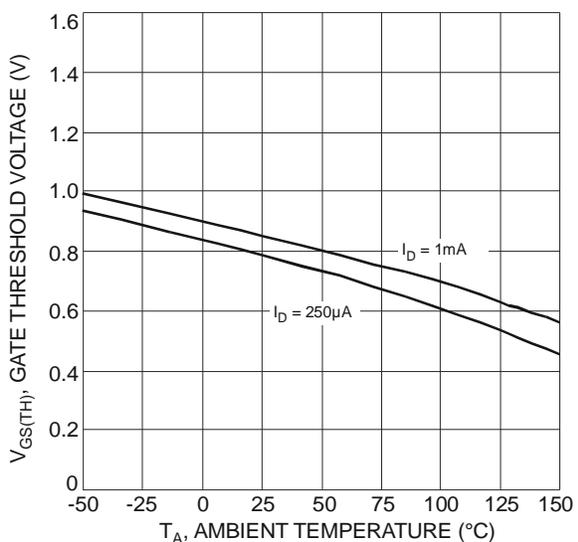


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

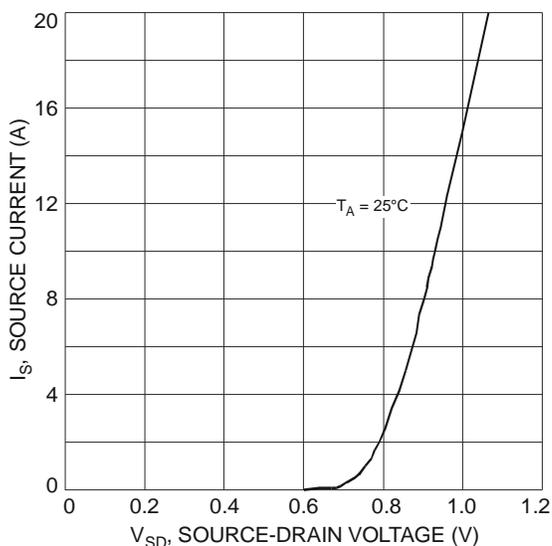


Fig. 8 Diode Forward Voltage vs. Current

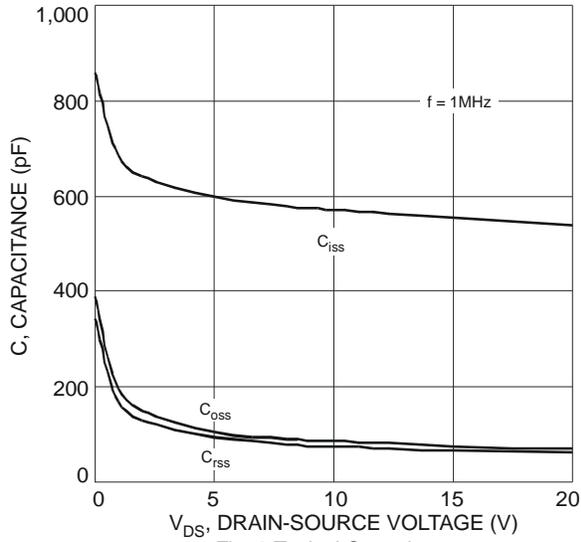


Fig. 9 Typical Capacitance

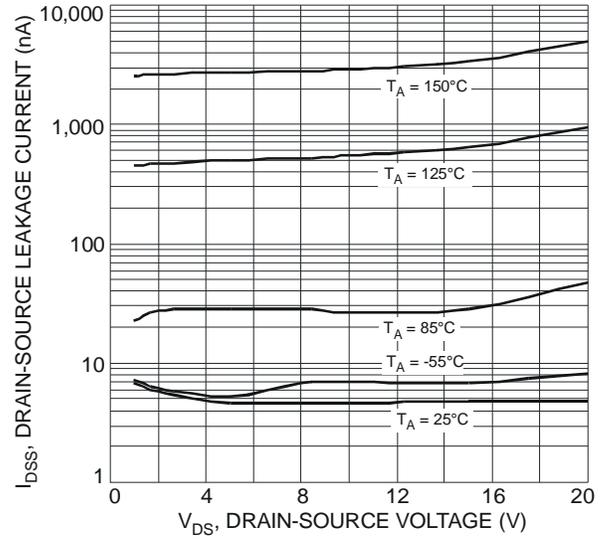


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

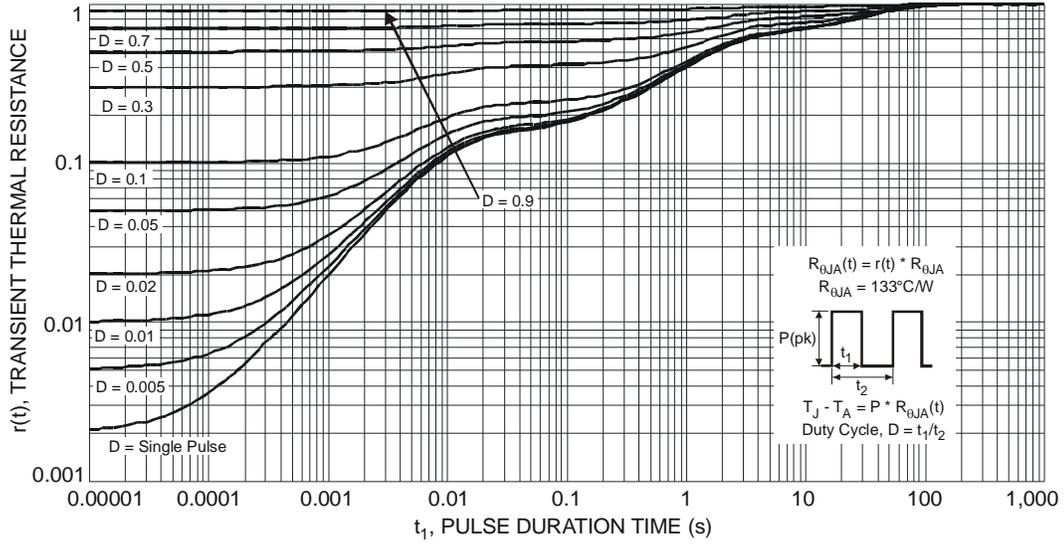
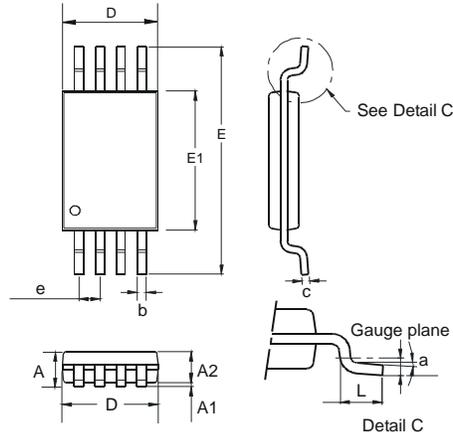


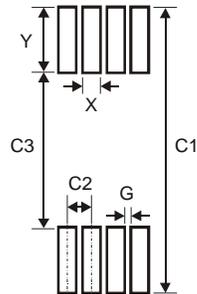
Fig. 11 Transient Thermal Response

Package Outline Dimensions



TSSOP-8L			
Dim	Min	Max	Typ
a	0.09	—	—
A	—	1.20	—
A1	0.05	0.15	—
A2	0.825	1.025	0.925
b	0.19	0.30	—
c	0.09	0.20	—
D	2.90	3.10	3.025
e	—	—	0.65
E	—	—	6.40
E1	4.30	4.50	4.425
L	0.45	0.75	0.60
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20